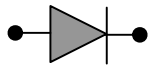
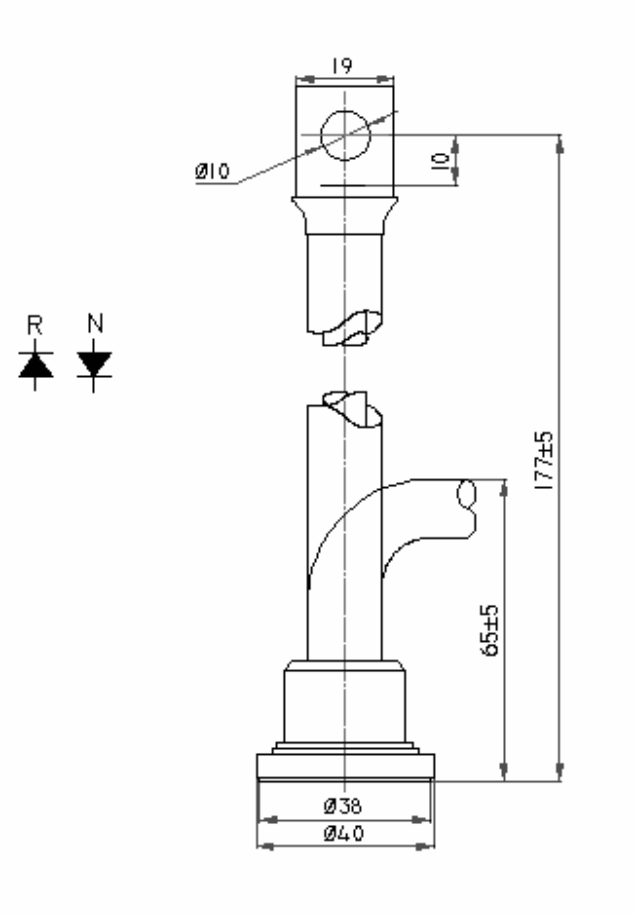
Rectifier Diode SXXHBN/HBR200

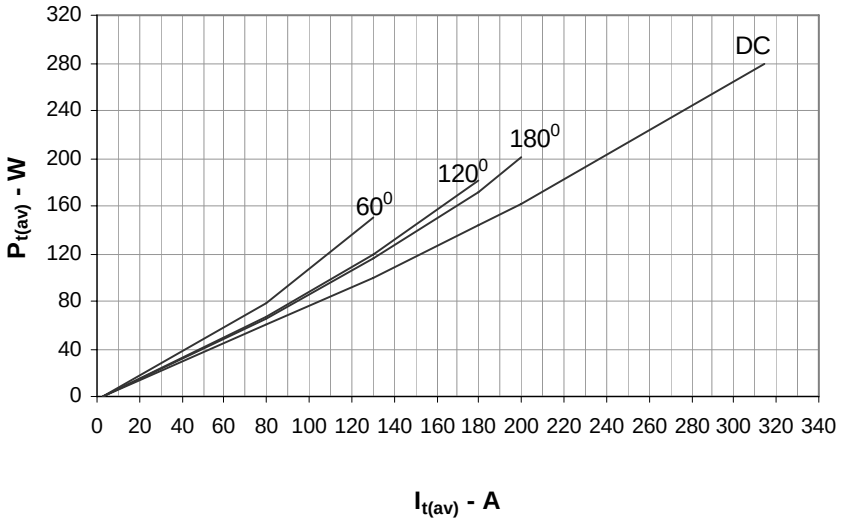


Symbol	Characteristics	Conditions	T_J(^{0}C)	Value	Unit
BLOCKING PARAMETERS					
V_{RRM}	Repetitive peak reverse voltage		180	200-1500	V
I_{RRM}	Repetitive peak reverse current	V = V_{RRM}	180	30	mA
CONDUCTING PARAMETERS					
$I_{F(AV)}$	Average on-state current	180 sine, 50H$_Z$, T_C = 130^{0}C		200	A
I_{RMS}	RMS on-state current			300	A
I_{FSM}	Non repetitive peak surge on-state current	Sine wave, 10mS without reverse voltage	180	4000	A
I^2t	Permissible surge energy			80.00	kA^{2}S
V_{FM}	Peak on-state voltage drop	On-state current = 630A	180	1.30	V
V_0	Typical forward conduction Threshold voltage		180	0.70	V
r_0	Typical forward slope resistance		180	0.60	mΩ
THERMAL & MECHANICAL PARAMETERS					
$R_{TH\ (J-C)}$	Thermal impedance, 180^0 conduction, Sine	Junction to case		0.24	^{0}C/W
$R_{TH\ (C-HK)}$	Thermal impedance	Case to heatsink		0.05	^{0}C/W
T_J	Maximum Permissible junction temperature			180	^{0}C
T_{STG}	Storage temperature range			-40 – 180	^{0}C
F	Mounting Torque			18	NM
W	Weight			160	gms

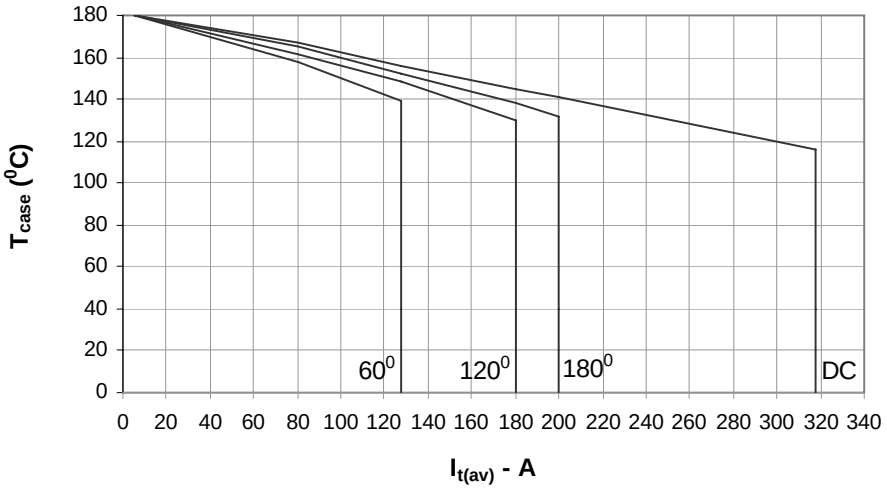


All dimensions in mm

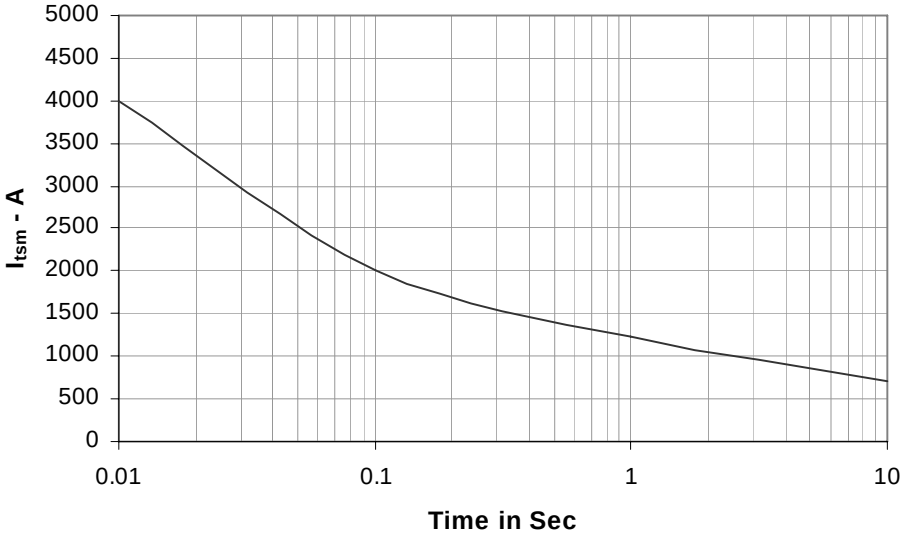
On State Power Loss



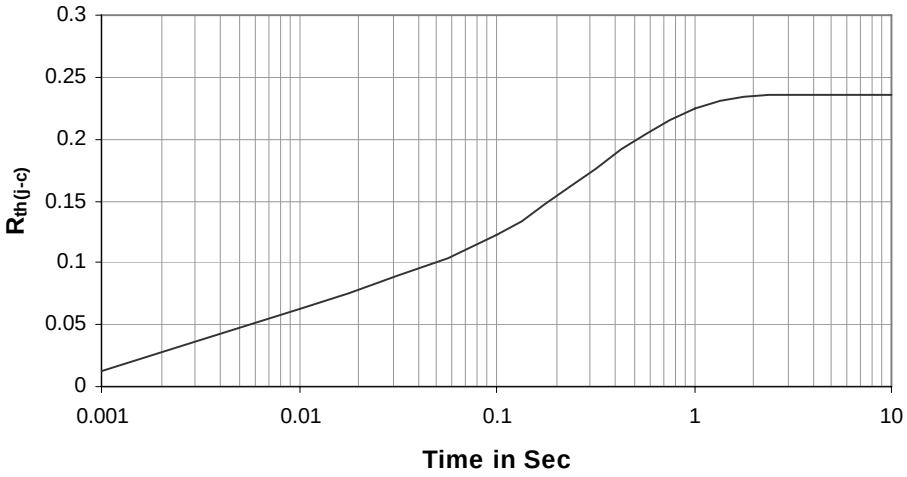
Maximum Permissible Case Temp



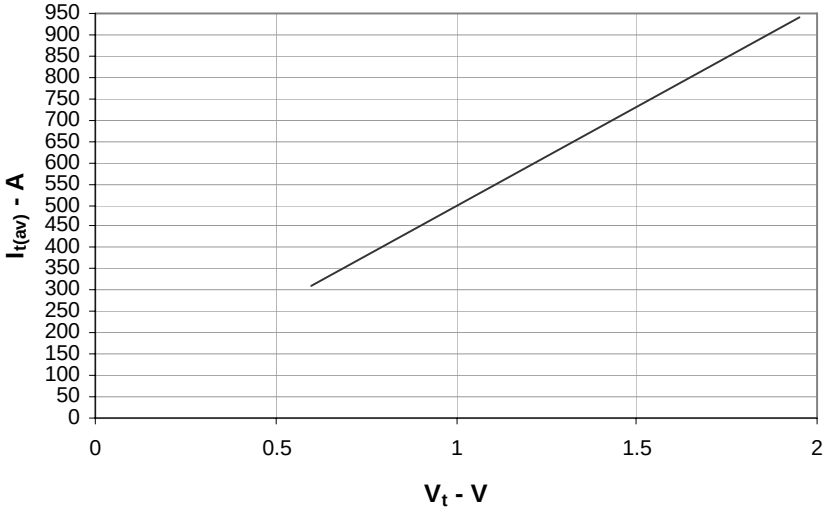
Max non repetitive Surge Current

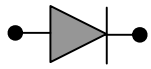


Transient Thermal Impedance Junction to Case



On State Characteristics





Ordering Information: -

S	XX	HBN / HBR	200
Hirect make Rectifier Diode	V_{RRM} = XX * 100 e.g.12 * 100 =1200V	HBN – Normal Polarity HBR – Reverse Polarity	$I_{F(AV)}$ = 200A

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